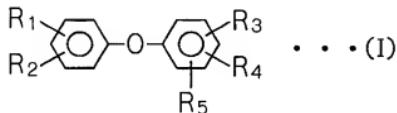


AMENDMENTS TO THE CLAIMS

1. (Currently Amended) A developer composition for resists, comprising an organic quaternary ammonium base as a main component,

said developer composition further comprising an anionic surfactant in an amount from 500 to 100,000 ppm represented by the following general formula (I):



wherein at least one of R₁ and R₂ represents an alkyl or alkoxy group having 5 to 18 carbon atoms and the other one represents a hydrogen atom, or an alkyl or alkoxy group having 5 to 18 carbon atoms, and at least one of R₃, R₄ and R₅ represents an ammonium sulfonate group or a sulfonic acid-substituted ammonium group and the others represent a hydrogen atom, an ammonium sulfonate group or a sulfonic acid-substituted ammonium group;

SO₄²⁻ in an amount from 10 to 10,000 ppm; and
a lower alcohol in an amount from 0.05 to 2.5% by mass; and
a halogen ion in an amount of 1,000 ppm or less.

2. (Canceled)

3. (Canceled)

4. (Previously presented) A method for formation of a resist pattern, comprising applying a resist composition on a substrate to form a resist layer, prebaking the resist layer, selectively exposing the prebaked resist layer to light, and alkali-developing the exposed resist layer with the developer composition for resists according to claim 1 to form a resist pattern.

5. (Previously presented) The developer composition for resists according to claim 1, wherein said lower alcohol has 1 to 5 carbon atoms.

6. (Previously presented) The developer composition for resists according to claim 5, wherein the lower alcohol is ethanol or methanol.

7. (New) The developer composition for resists according to claim 1, wherein the amount of said organic quaternary ammonium base is 0.1 to 10% by mass based on the developer composition for resists.

8. (New) The developer composition for resists according to claim 1, further comprising a halogen ion in an amount of 1,000 ppm or less.

9. (New) The developer composition for resists according to claim 8, wherein the amount of the halogen ion is from 300 to 1,000 ppm.